Diode Semiconductor Device - Page 1 of 1



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Inclosure N	lateriai:
Glass	
Overall Len	-
Between 0.2	293 inches and 0.357 inches
Terminal Le	ength:
	000 inches and 1.625 inches
Overall Dia	meter:
Between 0.2	215 inches and 0.235 inches
Electrode In	nternally-electrically Connected To Case:
Cathode	
Mounting N	lethod:
Terminal	
Features Pr	rovided:
Hermetically	v sealed case
Semicondu	ctor Material:
Silicon	
Voltage Rat	ting In Volts Per Characteristic:
41.0 breakc	lown voltage, dc
Current Rat	ting Per Characteristic:
28.00 ampe	res repetitive peak forward current
Power Rati	ng Per Characteristic:
1.0 watts sm	nall-signal input power, common-collector major
Maximum C	Operating Tempurature Per Measurement Point:
175.0 degre	es celsius ambient air
Test Data D	ocument:
81349-mil-p	rf-19500/500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in
specification	format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data o
certain envir	conmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Ty	/pe And Quantity:
2 uninsulate	d wire lead
Specificatio	on Data:
81349-mil-p	rf-19500/500 government specification
Shelf Life:	
N/a	
Unit Of Mea	asure:
Demilitariza	ation:
No	
Fiig:	
A110a0	
Mil-std (mil	itary Standard):
Mil-prf-1950	0 spec.